

TM15G02DF

N+P-Channel Enhancement Mosfet

General Description • Low $R_{DS(ON)}$ • RoHS and Halogen-Free Compliant Applications • Load switch • PWM	General Features N Channel $V_{DS} = 20V, I_D = 15A$ $R_{DS(ON)} = 13m\Omega (typ.) @ V_{GS} = 4.5V$ P Channel $V_{DS} = -20V, I_D = -14A$ $R_{DS(ON)} = 24m\Omega (typ.) @ V_{GS} = -4.5V$ 100% UIS Tested 100% R_g Tested
--	--



Absolute Maximum Ratings($T_A = 25^\circ C$ Unless Otherwise Noted)

Symbol	Parameter	Rating		Units
		N-Channel	P-Channel	
V_{DS}	Drain-Source Voltage	20	-20	V
V_{GS}	Gate-Source Voltage	± 12	± 12	V
$I_D @ T_A = 25^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	15	-14	A
$I_D @ T_A = 100^\circ C$	Continuous Drain Current, $V_{GS} @ 4.5V$	14	-12	A
I_{DM}	Pulsed Drain Current	60	-55	A
EAS	Single Pulse Avalanche Energy	80	65	mJ
$P_D @ T_C = 25^\circ C$	Total Power Dissipation	20.8	20.8	W
T_{STG}	Storage Temperature Range	-55 to 175	-55 to 175	$^\circ C$
T_J	Operating Junction Temperature Range	-55 to 175	-55 to 175	$^\circ C$

Thermal Data

Symbol	Parameter	Typ.	Max.	Unit
$R_{\theta JC}$	Thermal Resistance, Junction to Cast	6	6	$^\circ C/W$

TM15G02DF

N+P-Channel Enhancement Mosfet

N-Channel Electrical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =250 μ A	20	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =20V	---	---	1	μ A
I _{GSS}	Gate-Source Leakage Current	V _{GS} =± 12V, V _{DS} =0A	---	---	± 100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =250 μ A	0.5	0.75	1	V
R _{DS(on)}	Drain-Source On Resistance	V _{GS} =4.5V, I _D =4A	---	13	20	m Ω
		V _{GS} =2.5V, I _D =3A	---	20	30	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =10V, V _{GS} =0V, f=1MHz	---	676.4	---	pF
C _{oss}	Output Capacitance		---	121	---	
C _{rss}	Reverse Transfer Capacitance		---	108.1	---	
Q _g	Gate Charge	V _{GS} =0 to 4.5V , V _{DD} =10V I _D =3A	---	9.45	---	nC
Q _{gs}	Gate-Source Charge		---	1.69	---	
Q _{gd}	Gate-Drain Charge		---	2.62	---	
Switching Characteristics ⁴						
t _{d(on)}	Turn-On Delay Time	V _{DD} =10 V, I _D =3A, R _{REN} =3 Ω ,V _{GS} =4.5V	---	5.25	---	ns
t _r	Rise Time		---	16.8	---	ns
t _{d(off)}	Turn-Off Delay Time		---	24.15	---	ns
t _f	Fall Time		---	7.35	---	ns
Drain-Source Diode Characteristics						
I _S	Continuous Drain to Source Diode	VD=VG=0V	---	15		A
I _{SM}	Pulsed Drain to Source Diode ¹	VD=VG=0V	---	---	60	A
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V, I _S =6.8A	---	---	1.2	V

TM15G02DF

N+P-Channel Enhancement Mosfet

N-Typical Characteristics: ($T_C=25^\circ\text{C}$ unless otherwise noted)

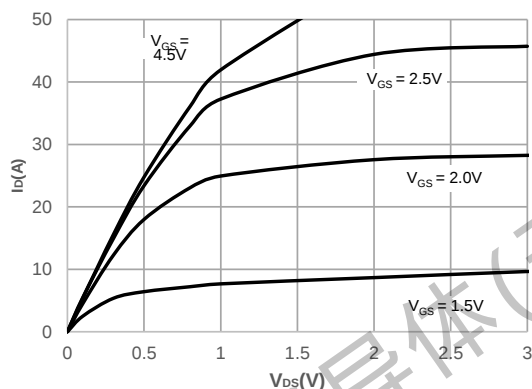


Figure 1: Output Characteristics

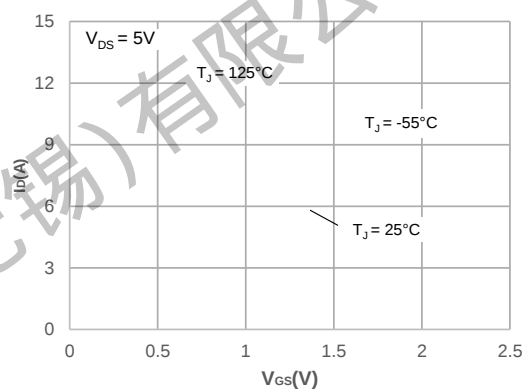


Figure 2: Typical Transfer Characteristics

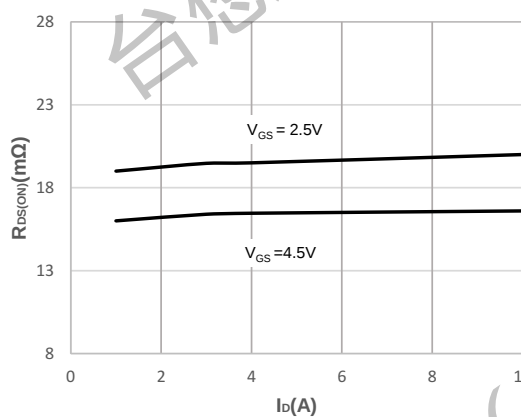


Figure 3: On-resistance vs. Drain Current

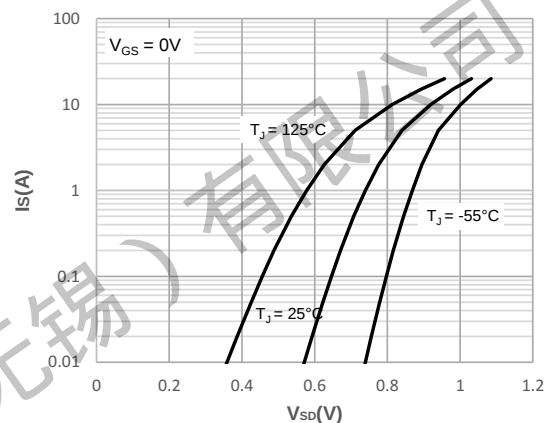


Figure 4: Body Diode Characteristics

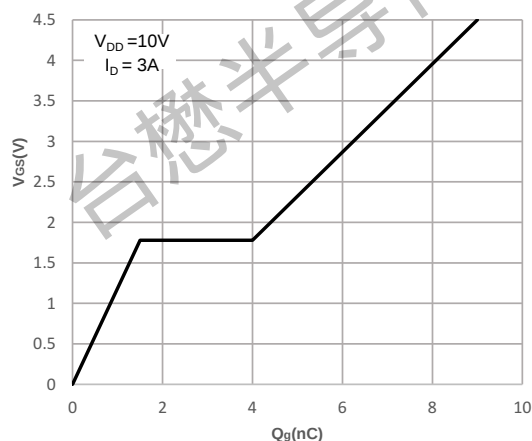


Figure 5: Gate Charge Characteristics

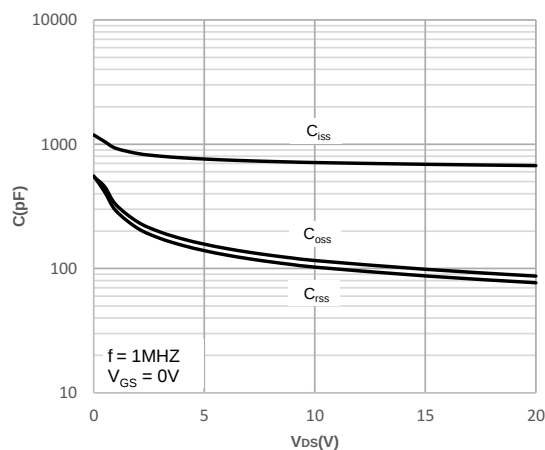


Figure 6: Capacitance Characteristics



TM15G02DF

N+P-Channel Enhancement Mosfet

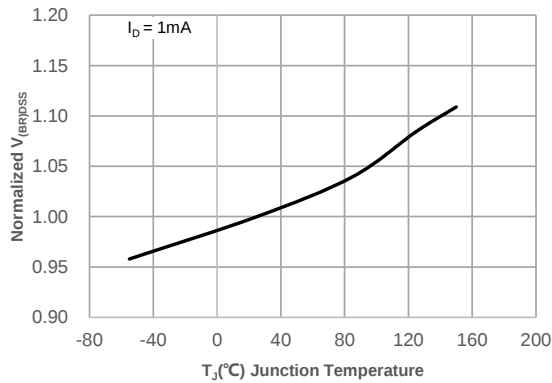


Figure 7: Normalized Breakdown voltage vs. Junction Temperature

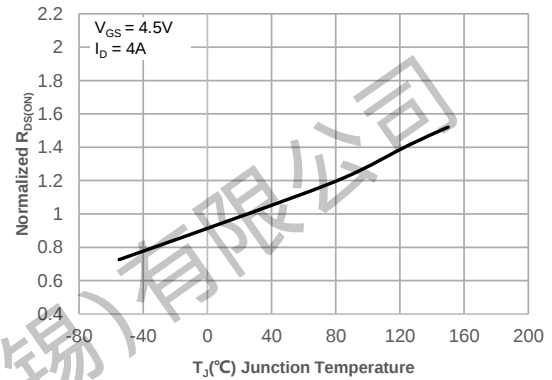


Figure 8: Normalized on Resistance vs. Junction Temperature

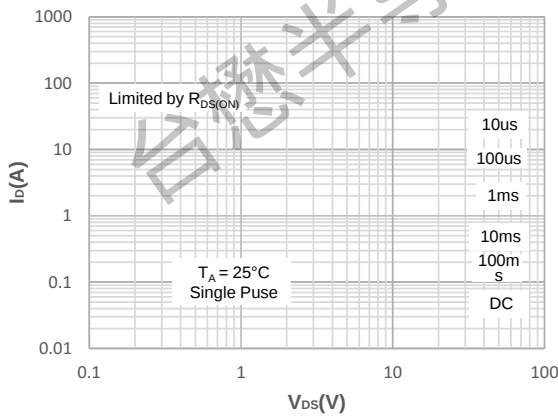


Figure 9: Maximum Safe Operating Area

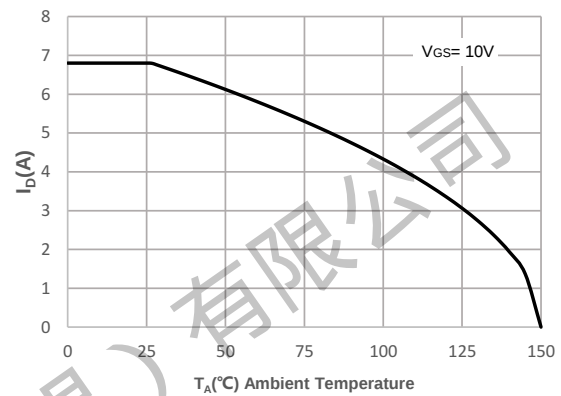


Figure 10: Maximum Continuous Drain Current vs. Ambient Temperature

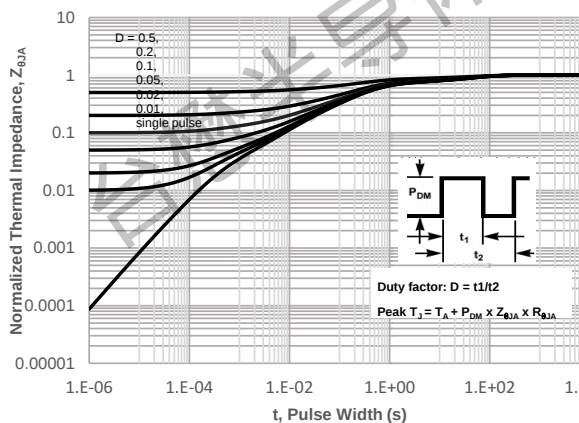


Figure 11: Normalized Maximum Transient Thermal Impedance

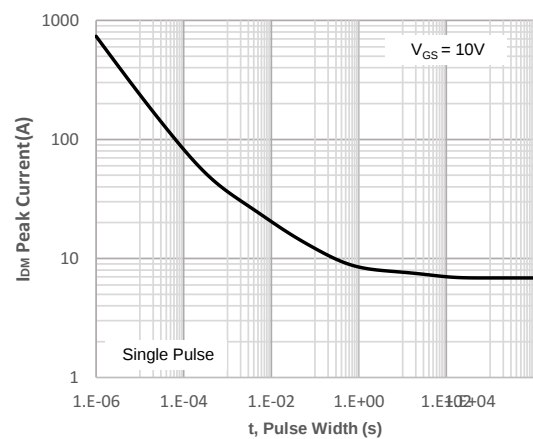


Figure 12: Peak Current Capacity

TM15G02DF

N+P-Channel Enhancement Mosfet

P-Channel Electrical Characteristics: (T_C=25°C unless otherwise noted)

Symbol	Parameter	Conditions	Min	Typ	Max	Units
Off Characteristics						
BV _{DSS}	Drain-Source Breakdown Voltage	V _{GS} =0V, I _D =-250 μA	-20	---	---	V
I _{DSS}	Zero Gate Voltage Drain Current	V _{GS} =0V, V _{DS} =-20V	---	---	-1	μA
I _{GSS}	Gate-Source Leakage Current	V _{GS} =±12V, V _{DS} =0A	---	---	±100	nA
On Characteristics						
V _{GS(th)}	Gate-Source Threshold Voltage	V _{GS} =V _{DS} , I _D =-250 μA	-0.3	-0.65	-1	V
R _{DS(on)}	Drain-Source On Resistance ³	V _{GS} =-4.5V, I _D =-4A	---	24	35	mΩ
		V _{GS} =-2.5V, I _D =-3A	---	35	50	
Dynamic Characteristics						
C _{iss}	Input Capacitance	V _{DS} =-10V, V _{GS} =0V, f=1MHz	---	788.5	---	pF
C _{oss}	Output Capacitance		---	138.6	---	
C _{rss}	Reverse Transfer Capacitance		---	89.25	---	
Switching Characteristics						
t _{d(on)}	Turn-On Delay Time	V _{DD} = -10V, I _D =-3.3A V _{GS} = -4.5V, R _{GEN} =1 Ω	---	10.5	---	ns
t _r	Rise Time		---	33.6	---	ns
t _{d(off)}	Turn-Off Delay Time		---	52.5	---	ns
t _f	Fall Time		---	53.55	---	ns
Q _g	Total Gate Charge	V _{GS} =-10V, V _{DD} =-4.5V, I _D =-2A	---	9.24	---	nC
Q _{gs}	Gate-Source Charge		---	1.47	---	nC
Q _{gd}	Gate-Drain “Miller” Charge		---	1.99	---	nC
Drain-Source Diode Characteristics						
I _S	Continuous Drain to Source Diode	V _D =V _G =0V	---	-14		A
I _{SM}	Pulsed Drain to Source Diode ¹		---	---	-55	---
V _{SD}	Source-Drain Diode Forward Voltage	V _{GS} =0V, I _S =-7A	---	---	-1.2	V

TM15G02DF

N+P-Channel Enhancement Mosfet

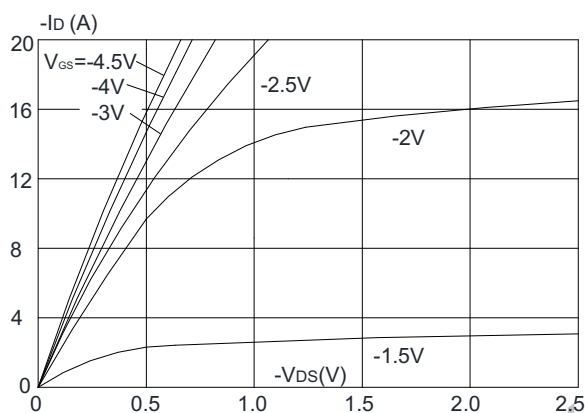


Figure 1: Output Characteristics

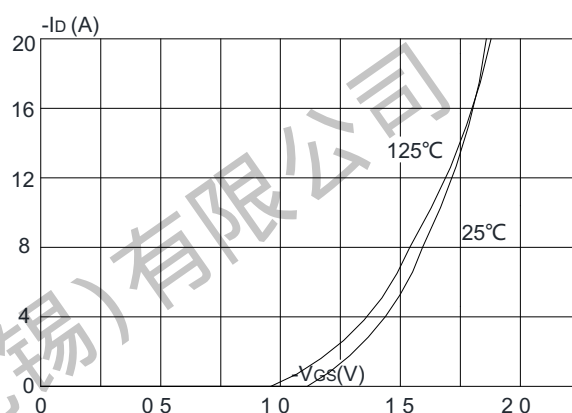


Figure 2: Typical Transfer Characteristics

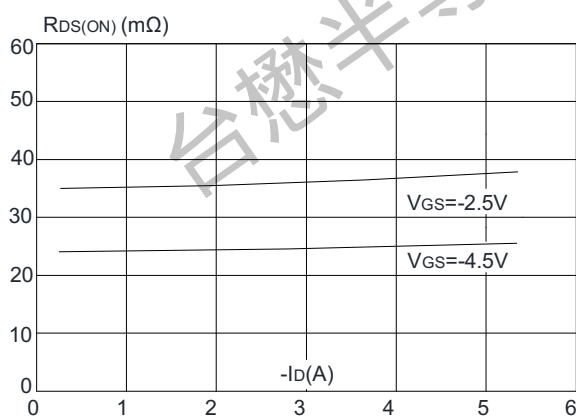


Figure 3: On-resistance vs. Drain Current

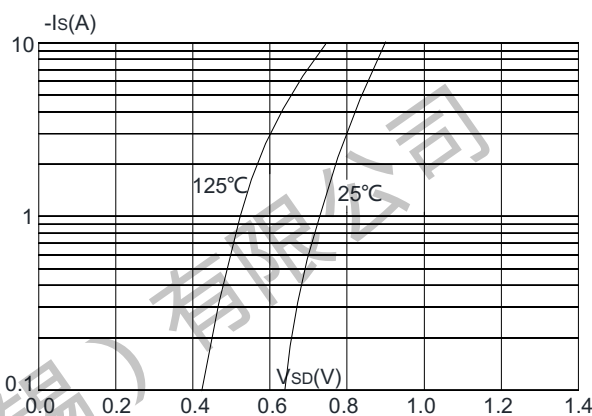


Figure 4: Body Diode Characteristics

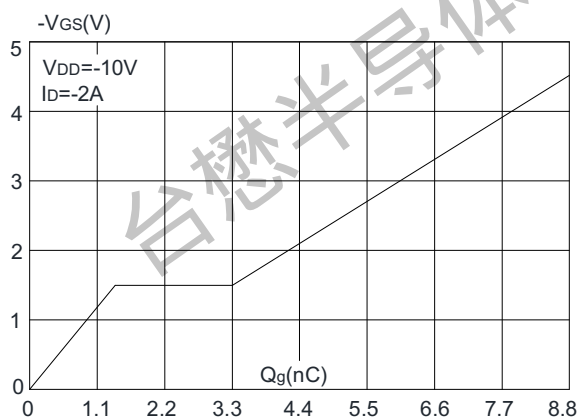


Figure 5: Gate Charge Characteristics

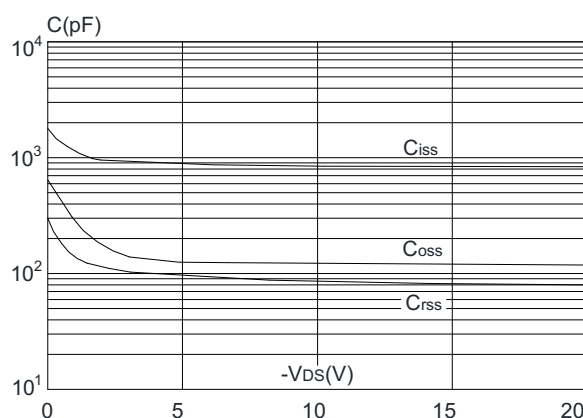


Figure 6: Capacitance Characteristics

TM15G02DF

N+P-Channel Enhancement Mosfet

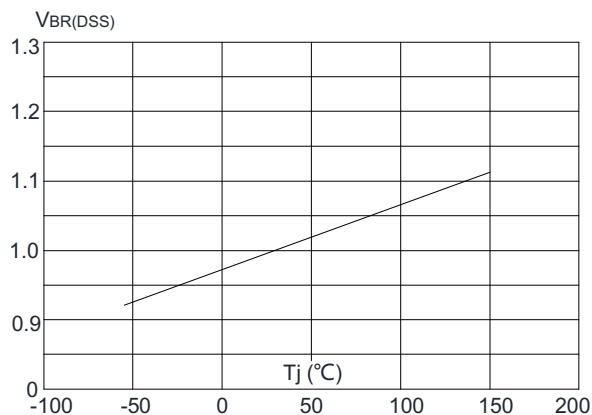


Figure 7: Normalized Breakdown Voltage vs. Junction Temperature

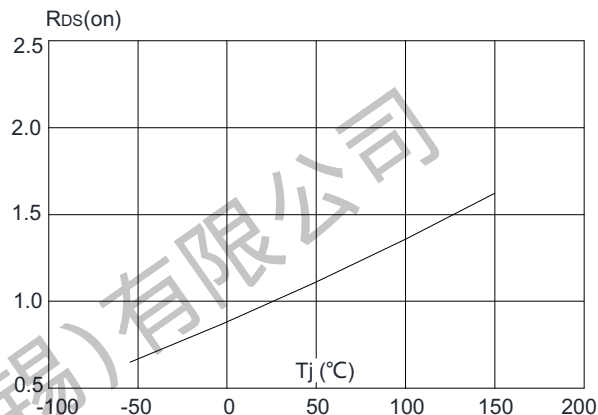


Figure 8: Normalized on Resistance vs. Junction Temperature

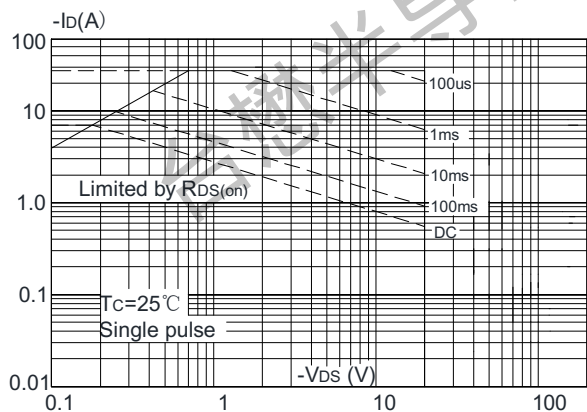


Figure 9: Maximum Safe Operating Area

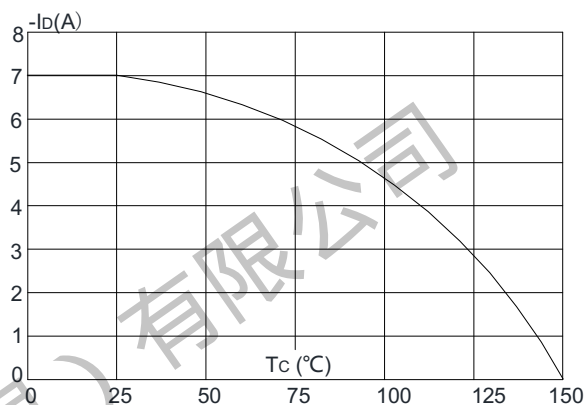


Figure 10: Maximum Continuous Drain Current vs. Case Temperature

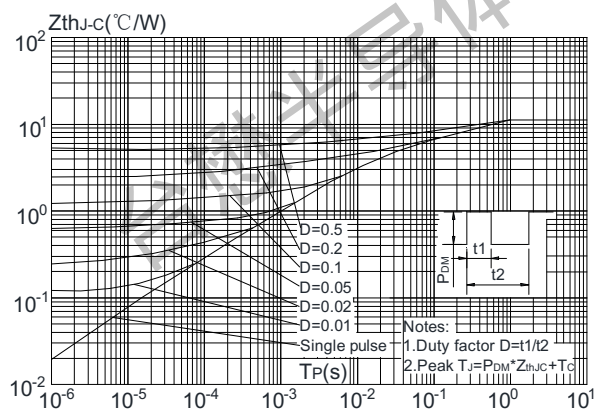
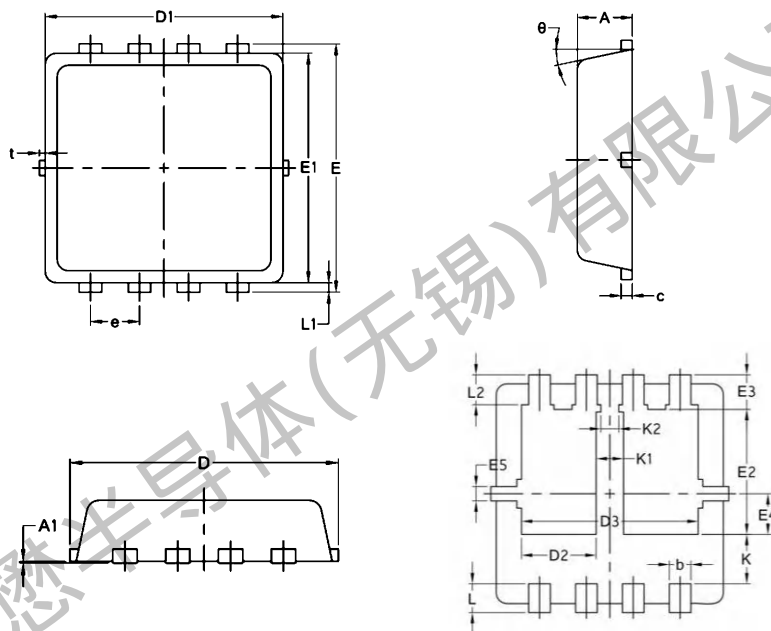


Figure 11: Maximum Effective Transient Thermal Impedance, Junction-to-Case

TM15G02DF

N+P-Channel Enhancement Mosfet

Package Mechanical Data:DFN3x3-8L

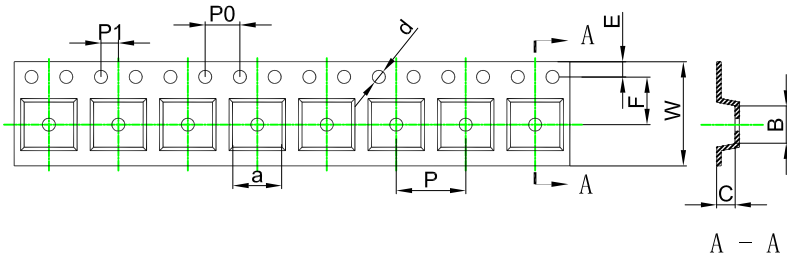


Symbol	Common		
	Mm		
	Min	Nom	Max
A	0.70	0.75	0.85
A1	/	/	0.05
b	0.25	0.30	0.39
c	0.14	0.152	0.20
D	3.20	3.30	3.45
D1	3.05	3.15	3.25
D2	0.84	1.04	1.24
D3	2.30	2.45	2.60
E	3.20	3.30	3.40
E1	2.95	3.05	3.15
E2	1.60	1.74	1.90
E3	0.28	0.48	0.65
E4	0.37	0.57	0.77
E5	0.10	0.20	0.30
e	0.60	0.65	0.70
K	0.50	0.69	0.80
K1	0.30	0.38	0.53
K2	0.15	0.25	0.35
L	0.30	0.40	0.50
L1	0.06	0.125	0.20
L2	0.27	0.42	0.57
t	0	0.075	0.13
Φ	10°	12°	14°

TM15G02DF

N+P-Channel Enhancement Mosfet

PDFN3×3-8L Embossed Carrier Tape



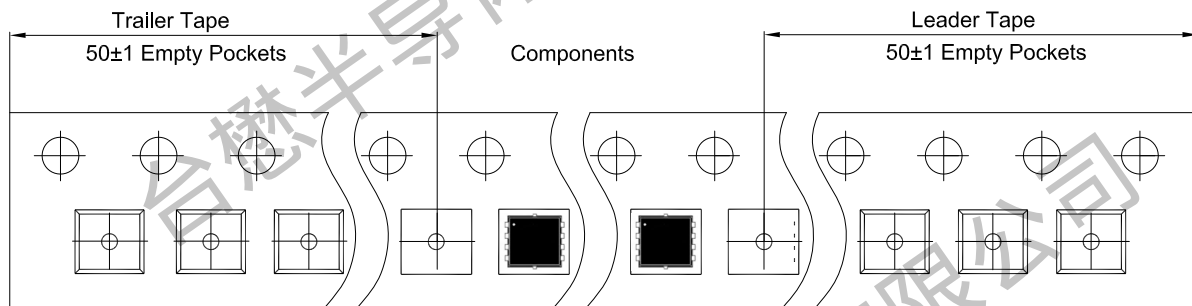
Packaging Description:

SOP-8L parts are shipped in tape. The carrier tape is made from a dissipative (carbon filled) polycarbonate resin. The cover tape is a multilayer film (Heat Activated Adhesive in nature) primarily composed of polyester film, adhesive layer, sealant, and anti-static sprayed agent. These reeled parts in standard option are shipped with 2,500 units per 13" or 33cm diameter reel. The reels are clear in color and is made of polystyrene plastic (anti-static coated).

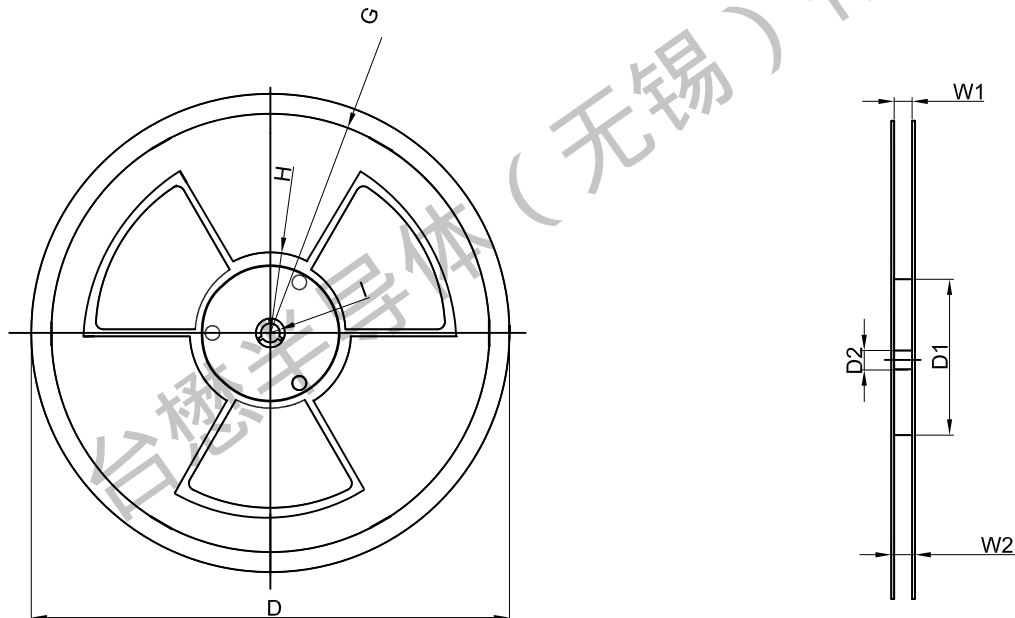
ALL DIM IN mm

Dimensions are in millimeter										
Pkg type	a	B	C	d	E	F	P0	P	P1	W
PDFN3×3-8L	6.40	5.40	2.10	Ø1.50	1.75	5.50	4.00	8.00	2.00	12.00

PDFN3×3-8L Tape Leader and Trailer



PDFN3×3-8L Reel



Dimensions are in millimeter								
Reel Option	D	D1	D2	G	H	I	W1	W2
13"Dia	Ø330.00	100.00	13.00	R135.00	R55.00	R6.50	12.00	14.00

REEL	Reel Size	Box	Box Size(mm)	Carton	Carton Size(mm)	G.W.(kg)
5,000 pcs	13 inch	10,000 pcs	370×355×52	50,000 pcs	400×360×368	

Important Notices and Disclaimers

- Tritech-MOS Technology Corp. reserves the right to change this document, its products, and specifications at any time without prior notice.
- Before final design, purchase, or use, customers should obtain and confirm the latest product information and specifications.
- Tritech-MOS Technology Corp. makes no warranties, representations or warranties regarding the suitability of its products for any specific purpose, and Tritech-MOS Technology Corp. does not assume any responsibility for application assistance or customer product design.
- Tritech-MOS Technology Corp. does not guarantee or assume any responsibility for the purchase or use of any unexpected or unauthorized products.
- Any intellectual property rights of Tritech-MOS Technology Corp. are not licensed through implicate or other means.
- Products of Tritech-MOS Technology Corp. are not included as critical components in life support equipment or systems without explicit written approval from Tritech-MOS Technology Corp.

Revision history:

Date	Rev	Description	Page
2023.06.08	23.06	Original	